DT06 d PCT/PTO 0 1 MAR 2005

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

CAPEWELL et al

International Appln. No.: PCT/GB2003/003514

Filed: Concurrently herewith

Attorney Dkt. No.: 58504.00037

For: FORMATION OF LATTICE-TUNING SEMICONDUCTOR SUBSTRATES

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Attention: PCT DO/EO/US

March 1, 2005

Sir:

This is an Information Disclosure Statement submitted under 37 C.F.R.1.97(b).

The references cited in the attached Form PTO-1449 were cited in the enclosed International Search Report issued by the European Patent Office in connection with the above international application. It is understood that the European Patent Office has sent a copy of each of the cited references to the U.S. Patent and Trademark Office. However, for the Examiner's convenience, the cited references are attached hereto. Also enclosed is a UK Search Report and a copy of each reference cited therein.

In view of the above, all requirements of 37 CFR 1.97 and all official guidelines pertaining to Information Disclosure Statements have been complied with, and it is

therefore respectfully requested that the Examiner consider the references and make them of record in this application.

In the event that there are any fees due with respect to the filing of this paper, please charge Counsel's Deposit Account No. 50-2222.

Respectfully submitted,

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Enclosures: PTO-1449 Form

International Search Report

UK Search Report 11 References

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Sheet 1 of 1

FORM PTO-1449

EPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

58504.00037 New Application

APPLICANT

CAPEWELL et al

FILING DATE

GROUP

March 1, 2005

Not yet assigned

U.S. PATENT DOCUMENTS

	T	T	0.5	11 DOCUMENTS		,	
EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
	AA	2002/0017642	02/14/02	Mizushima et al			
	AB	5,410,167	04/25/95	Saito			
	AC	5,238,869	08/24/93	Shichijo et al			
	AD	5,108,947	04/28/92	Demeester et al			
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·	AF						

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AG	WO 01/01465	01/04/01	WIPO			xx	
АН	EP 1 052 684 A1	11/15/00	European			xx	
ΑI	GB 2 215 514	09/20/89	United Kingdom			xx	
AJ	WO 99/14804	03/25/99	WIPO			xx	
AK	WO 99/38201	07/29/99	WIPO			xx	

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)					
	AL	"Molecular beam epitaxy of strained Si _{1-x} Ge _x layers on patterned substrates" 1993-06-01, Journal of Crystal Growth, North-Holland Publishing Co., Vol. 130, nos. 3/4, pages 611-616, Bugiel et al.			
	AM				
	AN				
EXAMINER			DATE CONSIDERED		

*EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.